

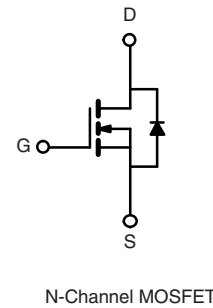
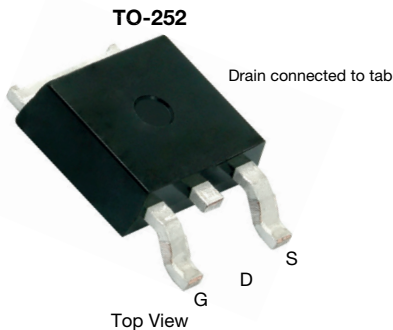
## Automotive N-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY <sup>d</sup>	
V <sub>DS</sub> (V)	60
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 10 V	0.042
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 4.5 V	0.060
I <sub>D</sub> (A)	15
Configuration	Single
Package	TO-252

### FEATURES

- TrenchFET® power MOSFET
- 100 % R<sub>g</sub> and UIS tested
- AEC-Q101 qualified
- Package with low thermal resistance
- Material categorization:  
for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current	I <sub>D</sub>	T <sub>C</sub> = 25 °C <sup>a</sup>	15
		T <sub>C</sub> = 125 °C	10
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	15	A
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	50	
Single Pulse Avalanche Current	I <sub>AS</sub>	18	
Single Pulse Avalanche Energy	E <sub>AS</sub>	16.2	mJ
Maximum Power Dissipation <sup>b</sup>	P <sub>D</sub>	T <sub>C</sub> = 25 °C	37
		T <sub>C</sub> = 125 °C	11
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R <sub>thJA</sub>	50	°C/W
Junction-to-Case (Drain)	R <sub>thJC</sub>	4	

### Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).



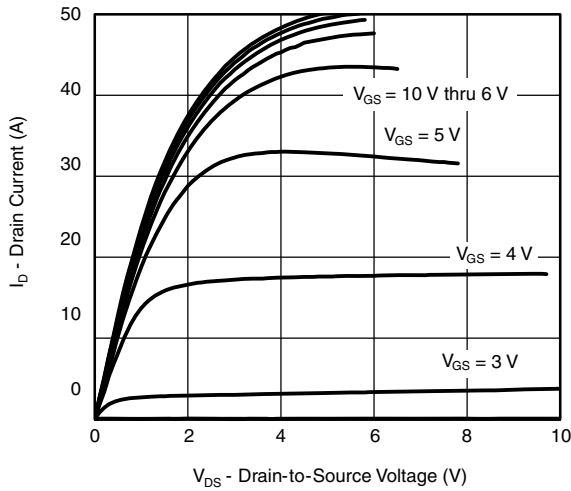
SPECIFICATIONS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		60	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		1.5	2	2.5	
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	150	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	30	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}$	-	0.036	0.042	$\Omega$
		$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.075	
		$V_{GS} = 10\text{ V}$	$I_D = 10\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.090	
		$V_{GS} = 4.5\text{ V}$	$I_D = 10\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	0.092	-	
		$V_{GS} = 4.5\text{ V}$	$I_D = 10\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	0.110	-	
		$V_{GS} = 4.5\text{ V}$	$I_D = 10\text{ A}$	-	0.048	0.060	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 6\text{ A}$		-	11	-	S
<b>Dynamic <sup>b</sup></b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	425	535	$\mu\text{F}$
Output Capacitance	$C_{oss}$			-	95	120	
Reverse Transfer Capacitance	$C_{rss}$			-	40	50	
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}, I_D = 15\text{ A}$	-	9.5	15	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			-	1.7	-	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	2.5	-	
Gate Resistance	$R_g$	f = 1 MHz		1.2	2.5	5.4	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong 15\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		-	5	8	ns
Rise Time <sup>c</sup>	$t_r$			-	10	15	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			-	13	20	
Fall Time <sup>c</sup>	$t_f$			-	8	12	
<b>Source-Drain Diode Ratings and Characteristics <sup>b</sup></b>							
Pulsed Current <sup>a</sup>	$I_{SM}$			-	-	50	A
Forward Voltage	$V_{SD}$	$I_F = 10\text{ A}, V_{GS} = 0\text{ V}$		-	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$I_F = 15\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		-	29	60	ns

**Notes**

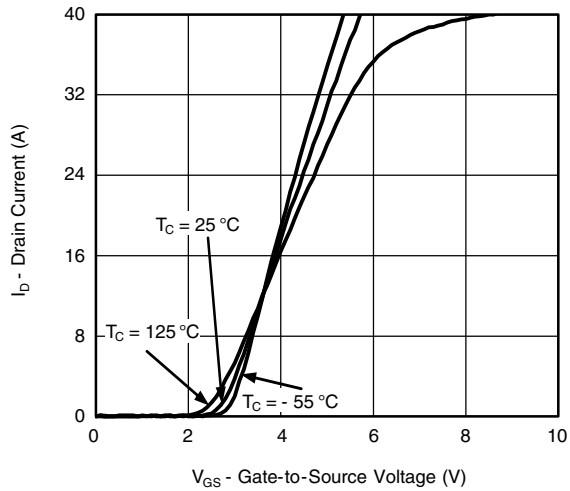
- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

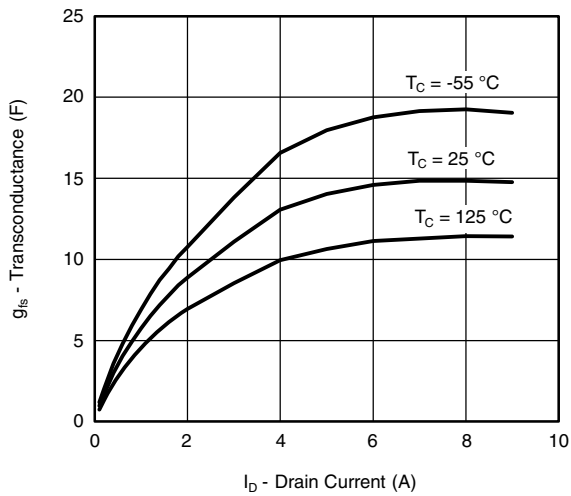
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



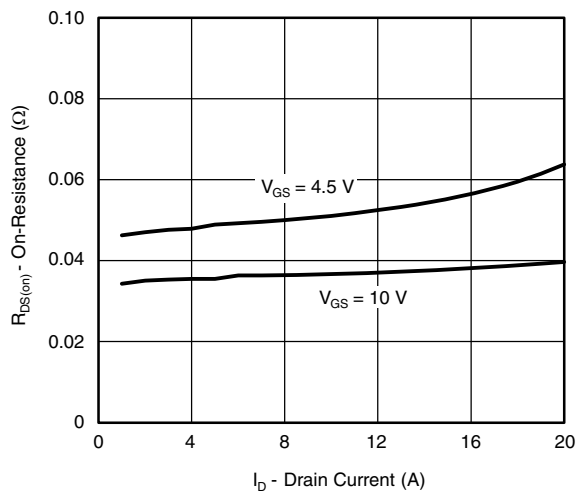
**Output Characteristics**



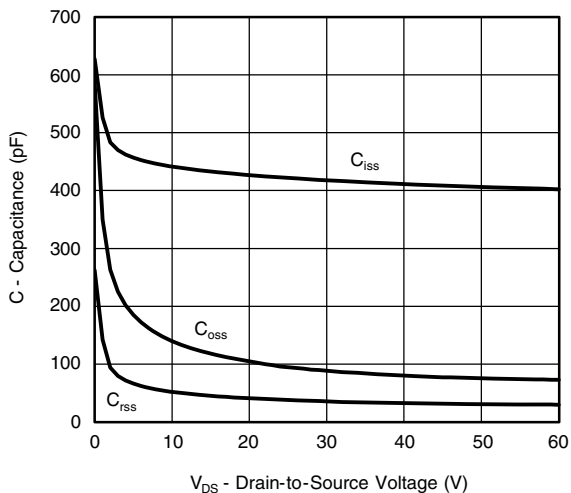
**Transfer Characteristics**



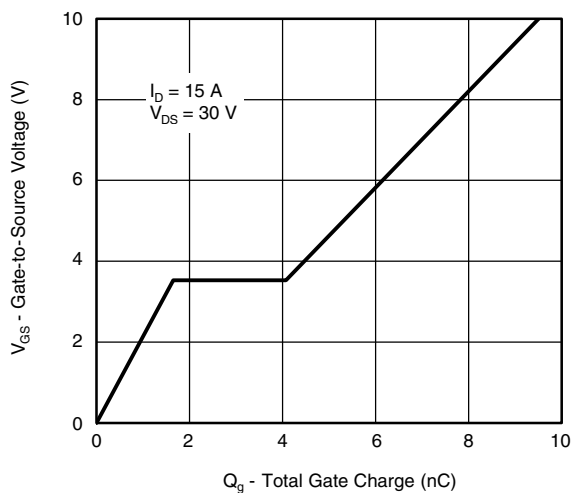
**Transconductance**



**On-Resistance vs. Drain Current**



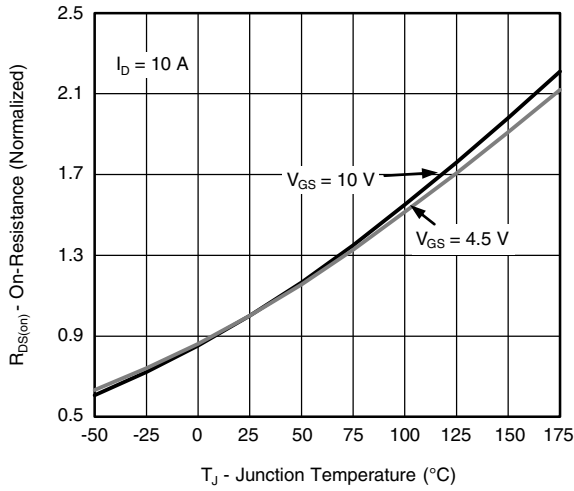
**Capacitance**



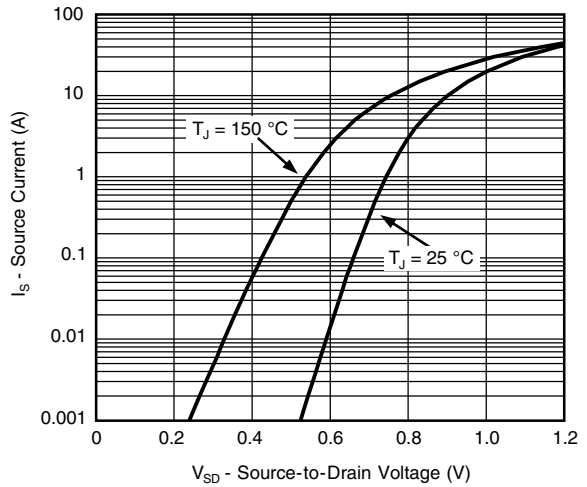
**Gate Charge**



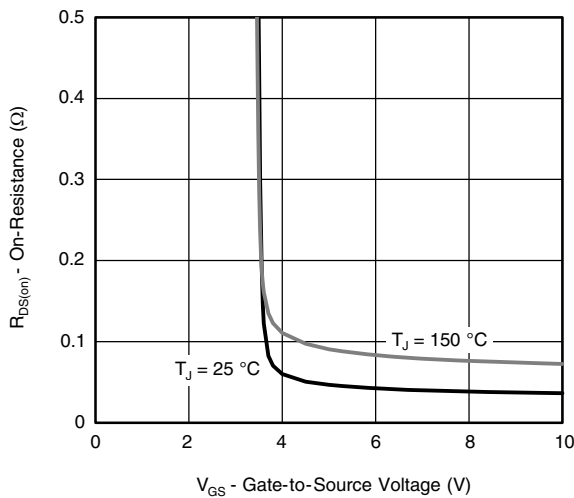
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



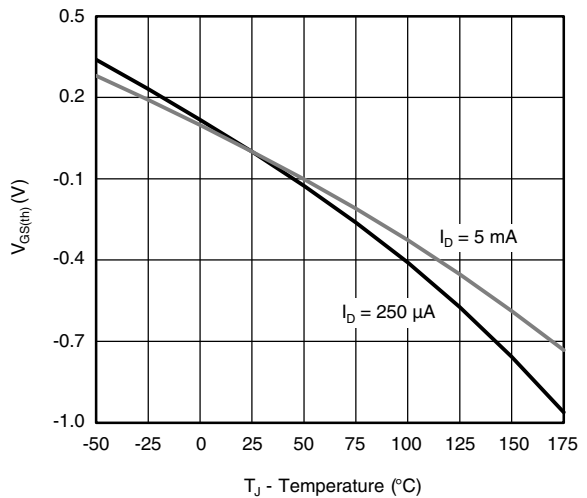
**On-Resistance vs. Junction Temperature**



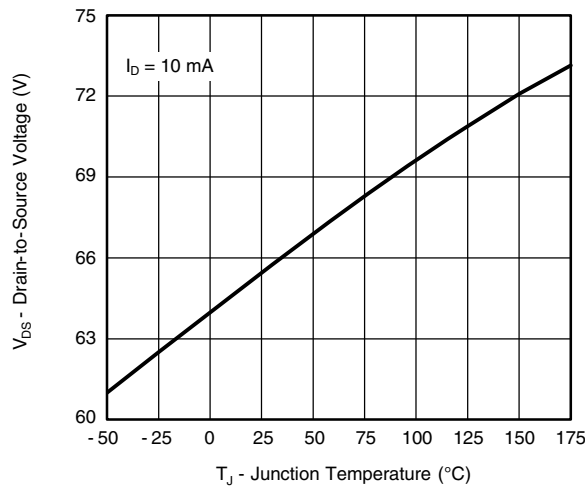
**Source Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



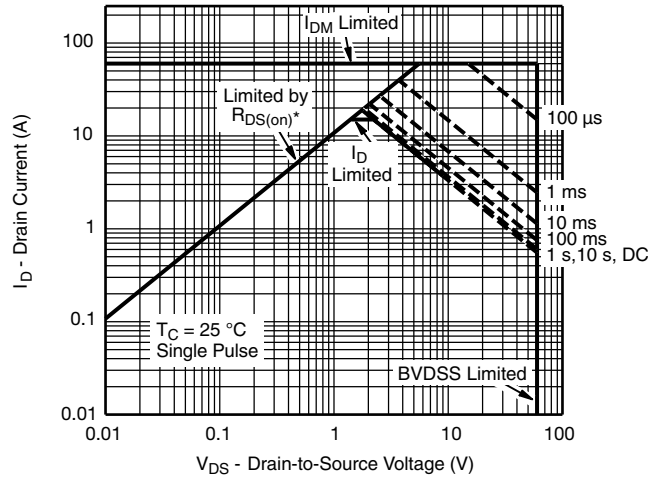
**Threshold Voltage**



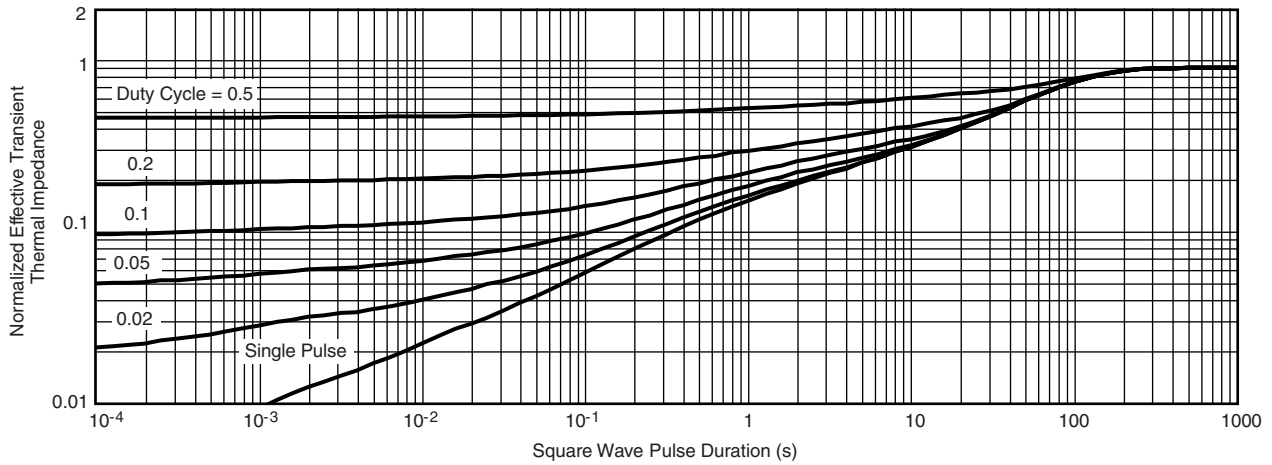
**On-Resistance vs. Junction Temperature**



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



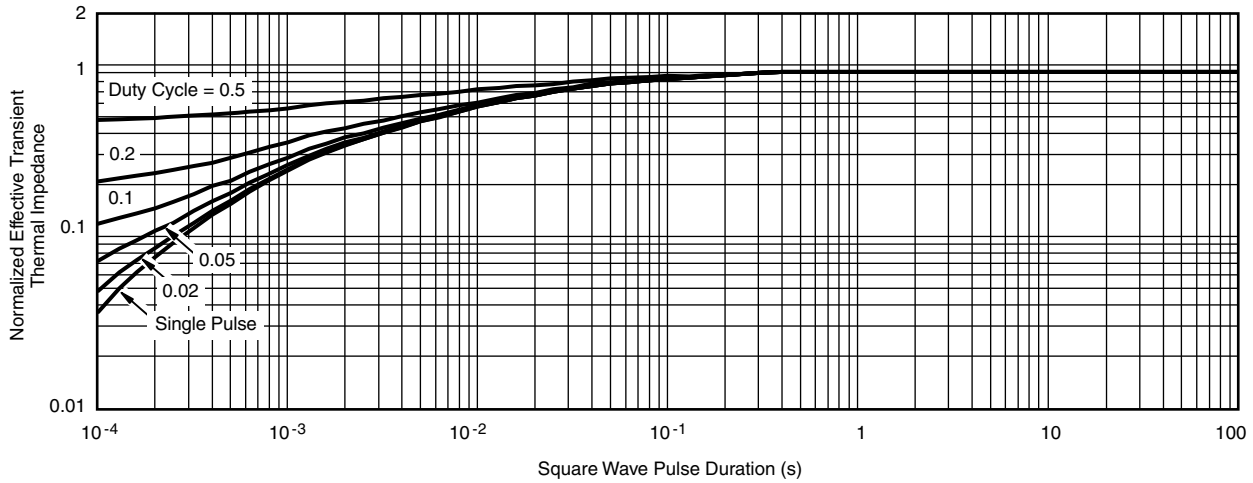
**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Case**

**Note**

- The characteristics shown in the two graphs
    - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
    - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)
- are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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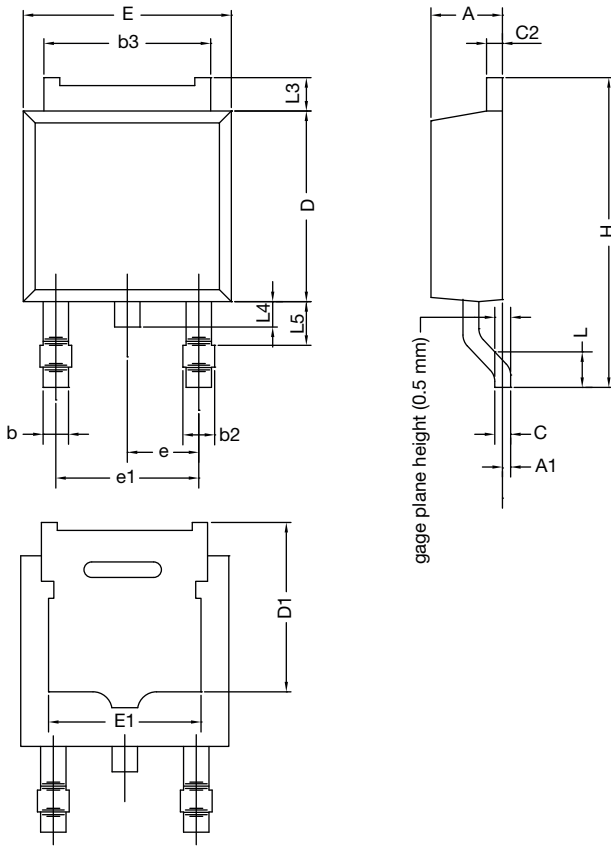
REVISION HISTORY <sup>a</sup>		
REVISION	DATE	DESCRIPTION OF CHANGE
G	04-Aug-15	• Revised R <sub>g</sub> minimum limit

**Note**

a. As of April 2014



### TO-252AA Case Outline



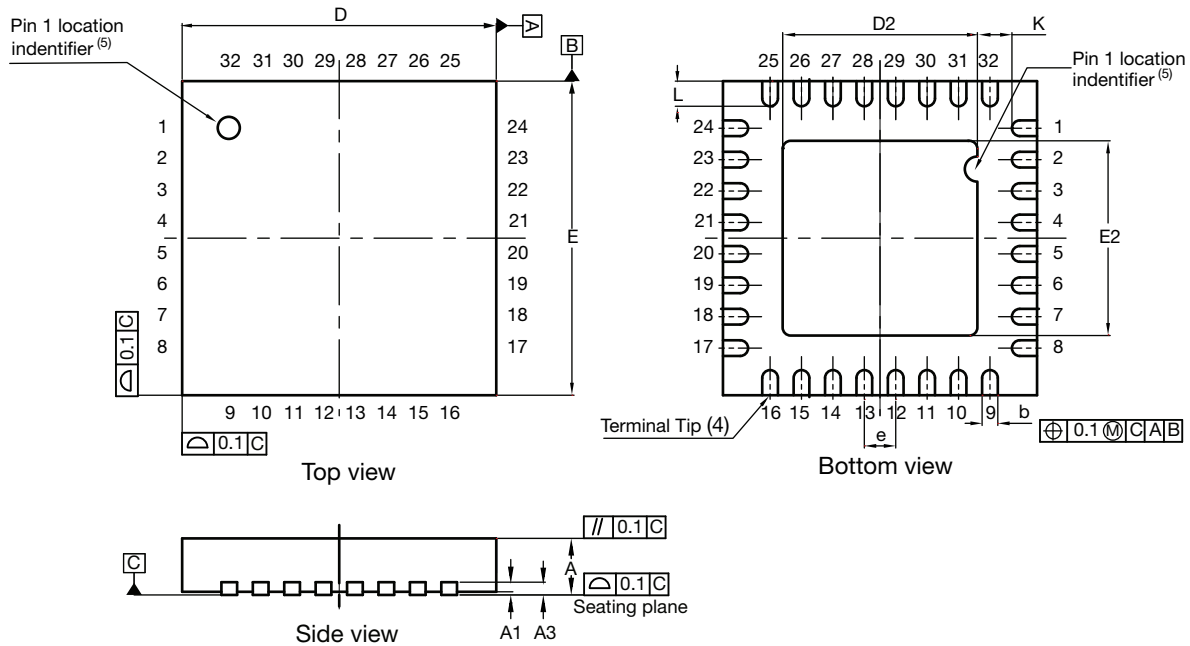
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019				

**Note**

- Dimension L3 is for reference only.



## QFN32 5 x 5 Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.75	0.85	0.95	0.029	0.033	0.037
A1	0.00	-	0.05	0.000	-	0.002
A3	0.20 ref.			0.008 ref.		
b	0.18	0.25	0.30	0.007	0.010	0.012
D	5.00 BSC			0.197 BSC		
D2	3.00	3.10	3.20	0.118	0.122	0.126
e	0.50 BSC			0.020 BSC		
E	5.00 BSC			0.197 BSC		
E2	3.00	3.10	3.20	0.118	0.122	0.126
K	0.20	-	-	0.008	-	-
L	0.30	0.40	0.50	0.012	0.016	0.020
N <sup>(3)</sup>	32			32		
Nd <sup>(3)</sup>	8			8		
Ne <sup>(3)</sup>	8			8		

**Notes**

- (1) Use millimeters as the primary measurement
- (2) Dimensioning and tolerances conform to ASME Y14.5M. - 1994
- (3) N is the number of terminals,  
Nd is the number of terminals in X-direction and  
Ne is the number of terminals in Y-direction.
- (4) Dimension b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip
- (5) The pin #1 identifier must be existed on the top surface of the package by using indentation mark or other feature of package body
- (6) Package warpage max. 0.05 mm

S14-2079-Rev. A, 20-Oct-14  
DWG: 6027

## RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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